

**VHF power transistor**

**BLW87**

**Description:**

N-P-N silicon planar epitaxial transistor intended for use in class-A, B and C operated mobile HF and VHF transmitters with a nominal supply voltage of 13.5 V. The transistor is resistance stabilized and is guaranteed to withstand severe load mismatch conditions with a supply over-voltage to 16.5 V.

**Features:**

It has a 3/8" flange envelope with a ceramic cap. All leads are isolated from the flange.

**Data:**

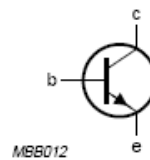
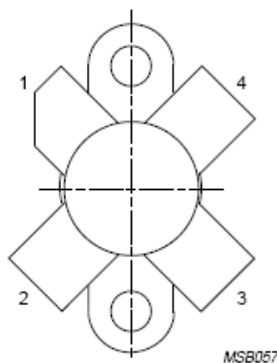
MODE OF OPERATION	V <sub>CE</sub> V	f MHz	P <sub>L</sub> W	G <sub>p</sub> dB	η %	$\bar{z}_i$ Ω	$\bar{Y}_L$ mS
c.w.	13,5	175	25	> 6	> 70	1,6 + j1,4	210 + j5,5

**RATINGS**

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Collector-emitter voltage (V <sub>BE</sub> = 0) peak value	V <sub>CESM</sub>	max.	36 V
Collector-emitter voltage (open base)	V <sub>CEO</sub>	max.	18 V
Emitter-base voltage (open collector)	V <sub>EBO</sub>	max.	4 V
Collector current (average)	I <sub>C(AV)</sub>	max.	6 A
Collector current (peak value); f > 1 MHz	I <sub>CM</sub>	max.	12 A
R.F. power dissipation (f > 1 MHz); T <sub>mb</sub> = 25 °C	P <sub>rf</sub>	max.	76 W
Storage temperature	T <sub>stg</sub>	-65 to + 150	°C
Operating junction temperature	T <sub>j</sub>	max.	200 °C

**Drawings:**



**PINNING - SOT123**

PIN	DESCRIPTION
1	collector
2	emitter
3	base
4	emitter

Fig.1 Simplified outline and symbol.